

## Two-Dimensional Transmission Line Matrix (TLM) Simulation of the Electromagnetic Fields in a Rectangular Section of a Discretized GaAs MESFET Channel with Arbitrary Doping Profile

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A two-dimensional lossy shunt TLM network is adapted to simulate the Maxwell field equations of a GaAs MESFET. By discretizing the channel into rectangular sections of single thickness, the new TLM technique is shown, with examples, that it can simulate the calculated electromagnetic fields of an arbitrarily doped channel section.

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